

**UTRON**

Rev. 1.3

UT62256C
32K X 8 BIT LOW POWER CMOS SRAM**REVISION HISTORY**

REVISION	DESCRIPTION	DATE
Rev. 0.9	Original.	Apr. 26,2001
Rev. 1.0	Revised - The test condition of I_{CC1} and I_{CC2} - Symbols CE#,OE# and WE# $\Rightarrow$ $\overline{CE}$, $\overline{OE}$ and $\overline{WE}$ - The ordering information of package ,STSOP-1 is revised as STSOP.	May. 14,2001
Rev. 1.1	Revised - Improve I_{DR} from 20 μ A to 10 μ A (LL-version , max.) - Package outline dimension	May 14,2002
Rev. 1.2	Revised - Add Standby Current $I_{SB1}=20\mu A$ for special requirement (LL-version , max.) - Ordering information in Standby Current column (maximum typical) - Standby Current in FEATURES section Rev.1.1 : 3mA (typical) normal Rev.1.2 : 0.3mA (typical) normal - Cycle time condition of I_{CC2} in DC electrical characteristics Rev.1.1 : $T_{cycle}=1ms$ Rev. 1.2 : $T_{cycle}=1\mu s$ - Waveforms - Add under/overshoot range of V_{IL} & V_{IH}	May 20,2002
Rev. 1.3	Add order information for lead free product	May 15,2003

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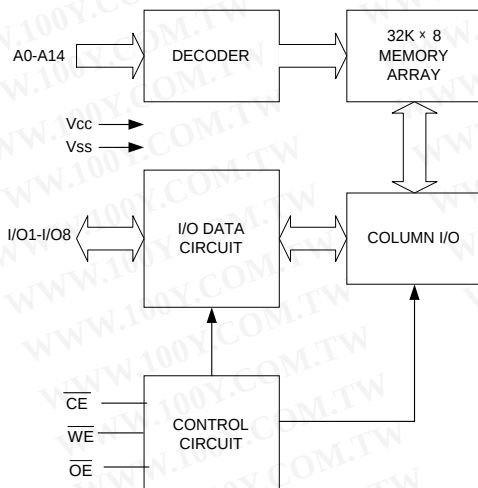
Rev. 1.3

UT62256C 32K X 8 BIT LOW POWER CMOS SRAM

FEATURES

- Access time : 35/70ns (max.)
- Low power consumption:
 - Operating : 40/30 mA (typical.)
 - Standby : 0.3mA (typical) normal
 - 2uA (typical) L-version
 - 1uA (typical) LL-version
- Single 5V power supply
- All inputs and outputs are TTL compatible
- Fully static operation
- Three state outputs
- Data retention voltage : 2V (min.)
- Package : 28-pin 600 mil PDIP
- 28-pin 330 mil SOP
- 28-pin 8mmx13.4mm STSOP

FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A14	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
V_{CC}	Power Supply
V_{SS}	Ground

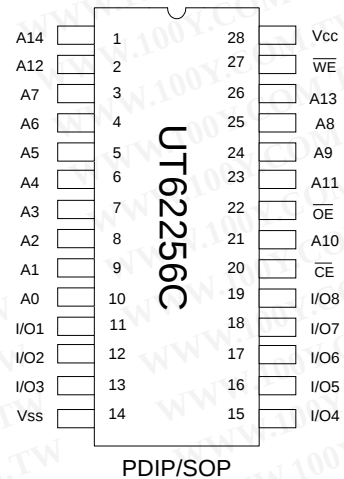
GENERAL DESCRIPTION

The UT62256C is a 262,144-bit low power CMOS static random access memory organized as 32,768 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology.

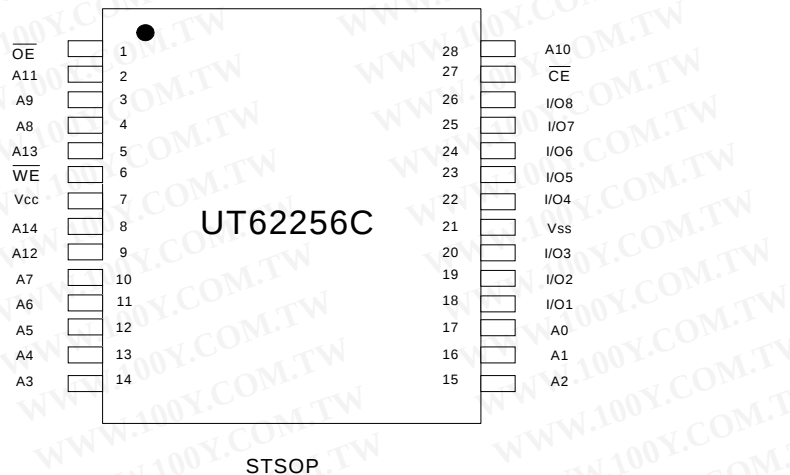
The UT62256C is designed for high-speed and low power application. It is particularly well suited for battery back-up nonvolatile memory application.

The UT62256C operates from a single 5V power supply and all inputs and outputs are fully TTL compatible

PIN CONFIGURATION



PDIP/SOP



STSOP



UTRON

Rev. 1.3

UT62256C

32K X 8 BIT LOW POWER CMOS SRAM

ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V_{SS}	V_{TERM}	-0.5 to +7.0	V
Operating Temperature	T_A	0 to +70	
Storage Temperature	T_{STG}	-65 to +150	
Power Dissipation	P_D	1	W
DC Output Current	I_{OUT}	50	mA
Soldering Temperature (under 10 sec)	T_{solder}	260	

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High - Z	I_{SB}, I_{SB1}
Output Disable	L	H	H	High - Z	I_{CC}, I_{CC1}, I_{CC2}
Read	L	L	H	D_{OUT}	I_{CC}, I_{CC1}, I_{CC2}
Write	L	X	L	D_{IN}	I_{CC}, I_{CC1}, I_{CC2}

Note: H = V_{IH} , L = V_{IL} , X = Don't care.

DC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5V \pm 10\%$, $T_A = 0$ to 70)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input High Voltage	V_{IH}^{*1}		2.2	-	$V_{CC} + 0.5$	V
Input Low Voltage	V_{IL}^{*2}		-0.5	-	0.8	V
Input Leakage Current	I_{LI}	$V_{SS} \quad V_{IN} \quad V_{CC}$	-1	-	1	μA
Output Leakage Current	I_{LO}	$V_{SS} \quad V_{IO} \quad V_{CC}$ $\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$	-1	-	1	μA
Output High Voltage	V_{OH}	$I_{OH} = -1mA$	2.4	-	-	V
Output Low Voltage	V_{OL}	$I_{OL} = 4mA$	-	-	0.4	V
Operating Power Supply Current	I_{CC}	$\overline{CE} = V_{IL}$, $I_{IO} = 0mA$, Cycle=Min.	-35	-	40	mA
			-70	-	30	mA
	I_{CC1}	$\overline{CE} = 0.2V$; $I_{IO} = 0mA$ other pins at 0.2V or $V_{CC} - 0.2V$	-	-	20	mA
	I_{CC2}		-	-	10	mA
Standby Power Supply Current	I_{SB}	$\overline{CE} = V_{IH}$	normal	1	10	mA
				0.3	5	mA
	I_{SB}	$\overline{CE} = V_{IH}$	-L/-LL	-	3	mA
	I_{SB1}	$\overline{CE} \quad V_{CC} - 0.2V$	-L	2	100	μA
			-LL	1	50 20 ^{*4}	μA

Notes:

1. Overshoot : $V_{CC} + 2.0V$ for pulse width less than 10ns.
2. Undershoot : $V_{SS} - 2.0V$ for pulse width less than 10ns.
3. Overshoot and Undershoot are sampled, not 100% tested.
4. $I_{SB1} = 20\mu A$ for special requirement.



UTRON

Rev. 1.3

UT62256C

32K X 8 BIT LOW POWER CMOS SRAM

CAPACITANCE ($T_A=25^\circ\text{C}$, $f=1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	C_{IN}	-	8	pF
Input/Output Capacitance	$C_{I/O}$	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 100\text{pF}$, $I_{OH}/I_{OL} = -1\text{mA}/4\text{mA}$

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5V \pm 10\%$, $T_A = 0^\circ\text{C}$ to 70°C)

(1) READ CYCLE

PARAMETER	SYMBOL	UT62256C-35		UT62256C-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	35	-	70	-	ns
Address Access Time	t_{AA}	-	35	-	70	ns
Chip Enable Access Time	t_{ACE}	-	35	-	70	ns
Output Enable Access Time	t_{OE}	-	25	-	35	ns
Chip Enable to Output in Low Z	t_{CLZ*}	10	-	10	-	ns
Output Enable to Output in Low Z	t_{OLZ*}	5	-	5	-	ns
Chip Disable to Output in High Z	t_{CHZ*}	-	25	-	35	ns
Output Disable to Output in High Z	t_{OHZ*}	-	25	-	35	ns
Output Hold from Address Change	t_{OH}	5	-	5	-	ns

(2) WRITE CYCLE

PARAMETER	SYMBOL	UT62256C-35		UT62256C-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	35	-	70	-	ns
Address Valid to End of Write	t_{AW}	30	-	60	-	ns
Chip Enable to End of Write	t_{CW}	30	-	60	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	ns
Write Pulse Width	t_{WP}	25	-	50	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	20	-	30	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	ns
Output Active from End of Write	t_{OW*}	5	-	5	-	ns
Write to Output in High Z	t_{WHZ*}	-	15	-	25	ns

*These parameters are guaranteed by device characterization, but not production tested.



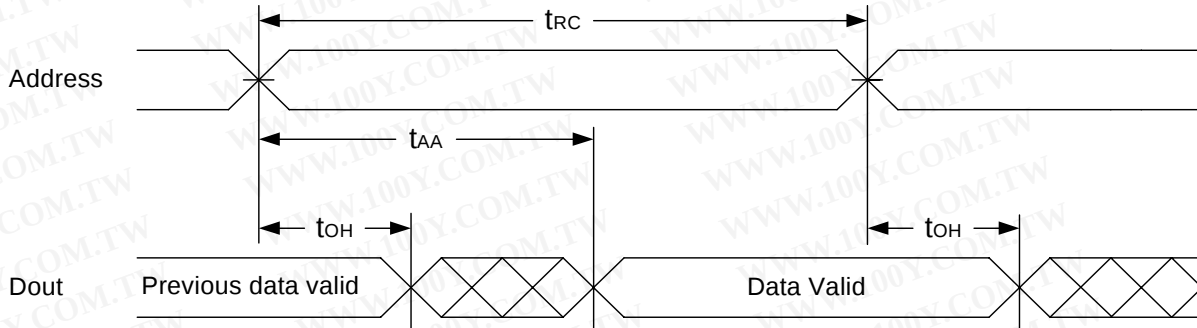
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Rev. 1.3

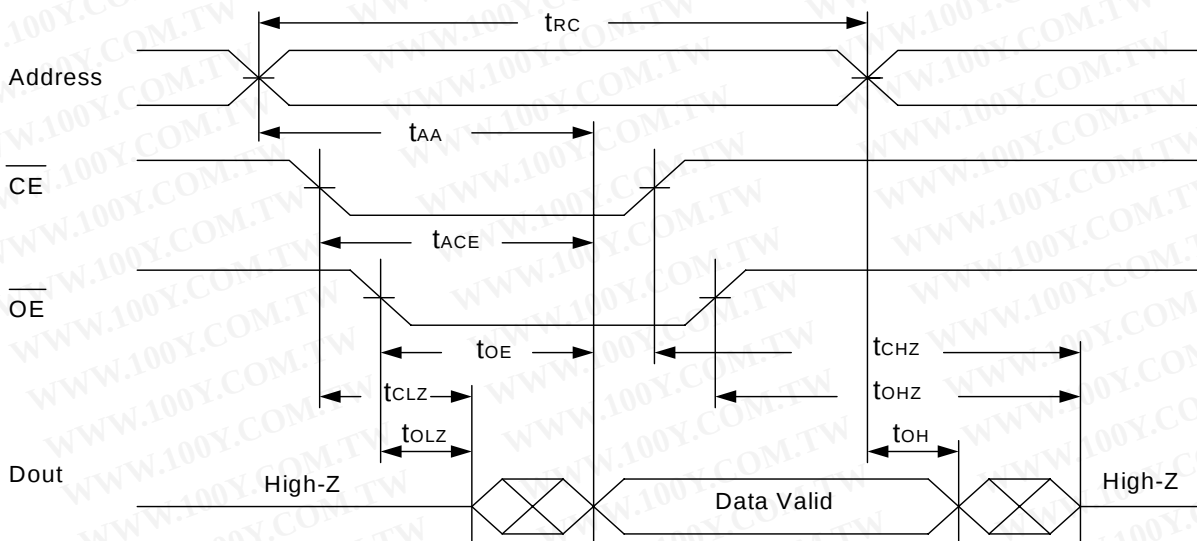
UT62256C
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TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 ($\overline{CE}$ and $\overline{OE}$ Controlled) (1,3,4,5)



Notes :

1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected $\overline{OE}$ = low, $\overline{CE}$ = low.
3. Address must be valid prior to or coincident with $\overline{CE}$ = low.; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ} , t_{OLZ} , t_{CHZ} and t_{OHZ} are specified with C_L = 5pF. Transition is measured ± 500 mV from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{OHZ} is less than t_{OLZ} .



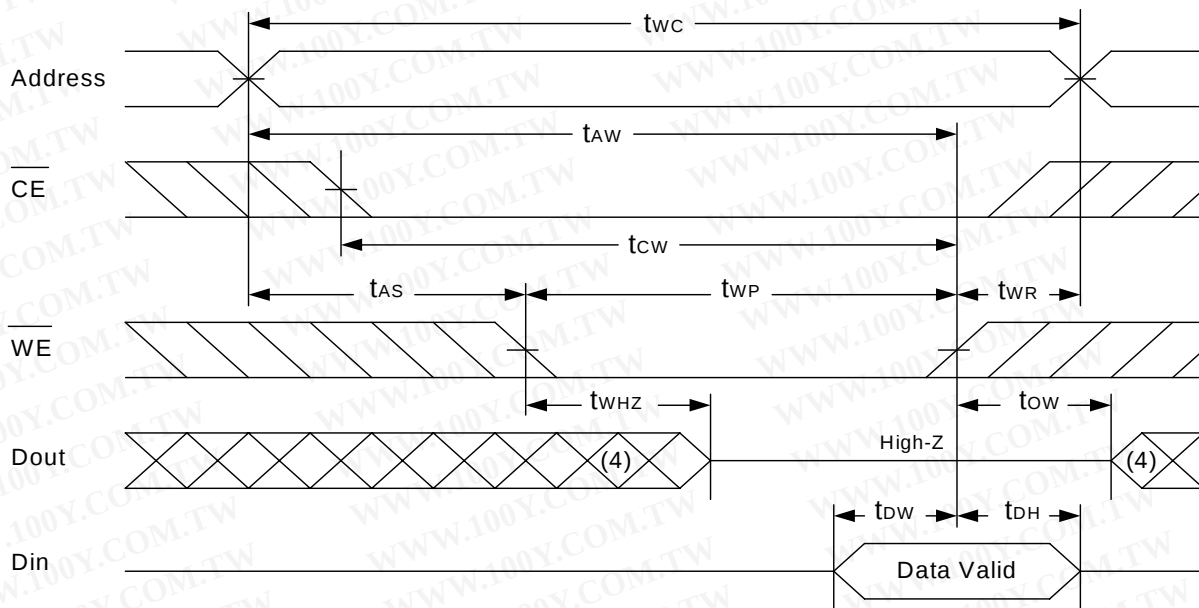
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Rev. 1.3

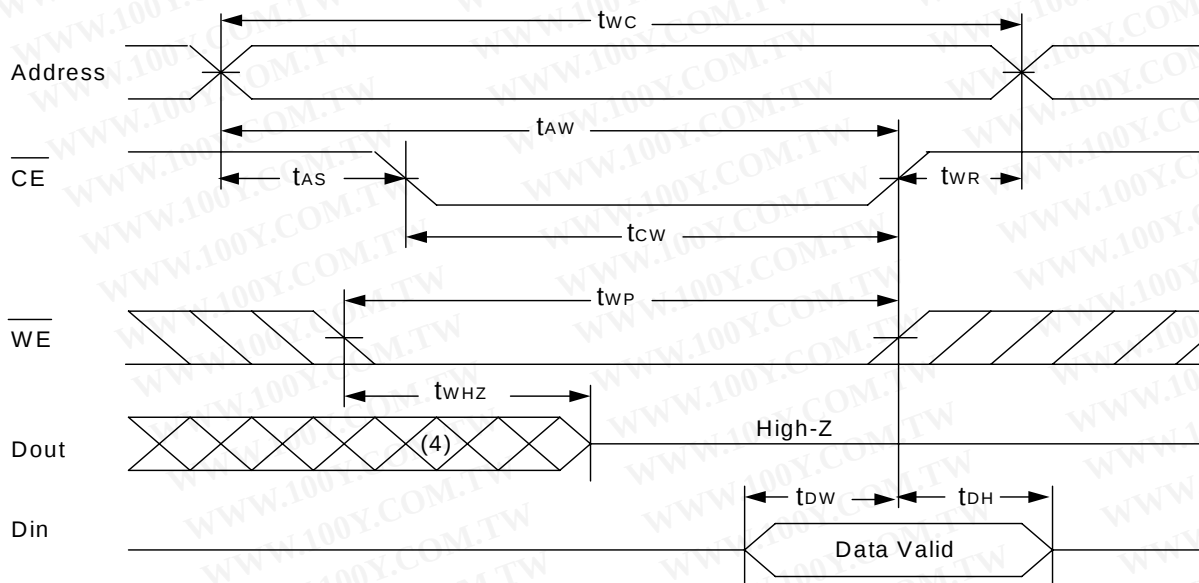
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32K X 8 BIT LOW POWER CMOS SRAM

WRITE CYCLE 1 ($\overline{WE}$ Controlled) (1,2,3,5,6)



WRITE CYCLE 2 ($\overline{CE}$ Controlled) (1,2,5,6)





UTRON

Rev. 1.3

UT62256C 32K X 8 BIT LOW POWER CMOS SRAM

Notes :

1. $\overline{WE}$, $\overline{CE}$ must be high during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE}$, low $\overline{WE}$.
3. During a $\overline{WE}$ controlled write cycle with $\overline{OE}$ low, t_{WP} must be greater than $t_{WHZ} + t_{OW}$ to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE}$ low transition occurs simultaneously with or after $\overline{WE}$ low transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.

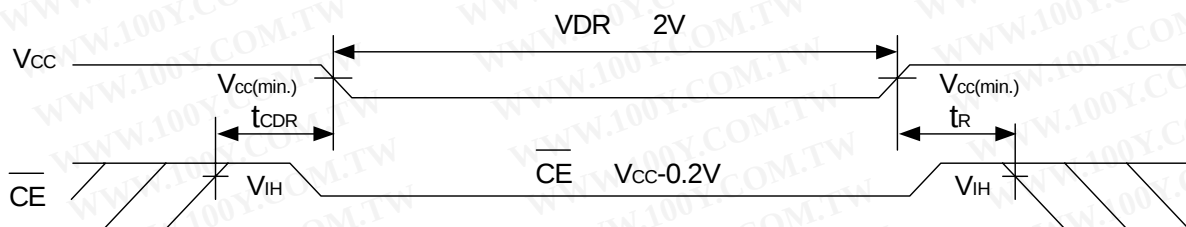
DATA RETENTION CHARACTERISTICS ($T_A = 0$ to 70)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	V_{DR}	$\overline{CE}$ $V_{CC}-0.2V$	2.0	-	5.5	V
Data Retention Current	I_{DR}	$V_{CC}=3V$ $\overline{CE}$ $V_{CC}-0.2V$	- L	1	50	μA
			- LL	0.5	10	μA
Chip Disable to Data Retention Time	t_{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t_R		t_{RC*}	-	-	ns

t_{RC*} = Read Cycle Time

DATA RETENTION WAVEFORM

Low Vcc Data Retention Waveform (1) ($\overline{CE}$ controlled)





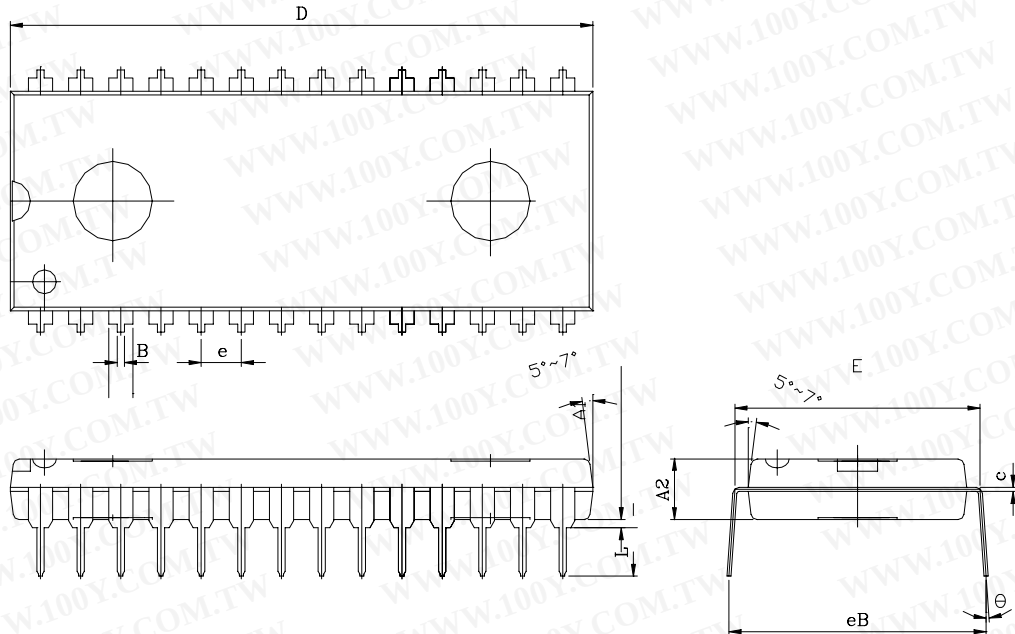
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Rev. 1.3

UT62256C
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PACKAGE OUTLINE DIMENSION

28 pin 600 mil PDIP Package Outline Dimension



SYMBOL	UNIT	INCH(BASE)	MM(REF)
A1		0.010(MIN)	0.254(MIN)
A2		0.150±0.001	3.810±0.254
B		0.018±0.005	0.457±0.127
c		0.010±0.004	0.254±0.102
D		1.460±0.005	37.084±0.127
E		0.600±0.010	15.240±0.254
e		0.100 (TYP)	2.540(TYP)
eB		0.640±0.03	16.256±0.762
L		0.130±0.010	3.302±0.254
θ		0°~15°	0°~15°

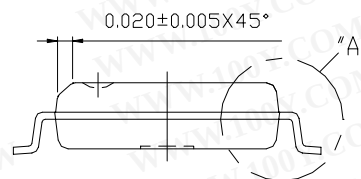
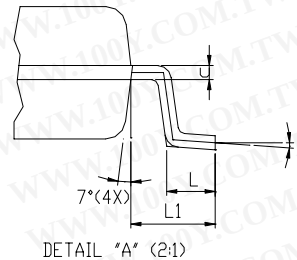
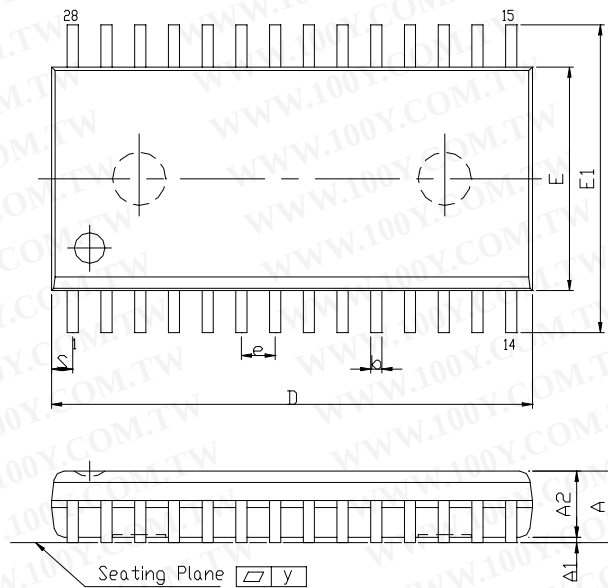


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Rev. 1.3

UT62256C 32K X 8 BIT LOW POWER CMOS SRAM

28 pin 330 mil SOP Package Outline Dimension



SYMBOL	UNIT	INCH(BASE)	MM(REF)
A		0.112 (MAX)	2.845 (MAX)
A1		0.004(MIN)	0.102(MIN)
A2		0.098±0.005	2.489±0.127
b		0.016 (TYP)	0.406(TYP)
c		0.010 (TYP)	0.254(TYP)
D		0.713±0.005	18.110±0.127
E		0.331±0.005	8.407±0.127
E1		0.465±0.012	11.811±0.305
e		0.050 (TYP)	1.270(TYP)
L		0.0404±0.008	1.0255±0.203
L1		0.067±0.008	1.702 ±0.203
S		0.047 (MAX)	1.194 (MAX)
y		0.003(MAX)	0.076(MAX)
θ		0° 10°	0° 10°

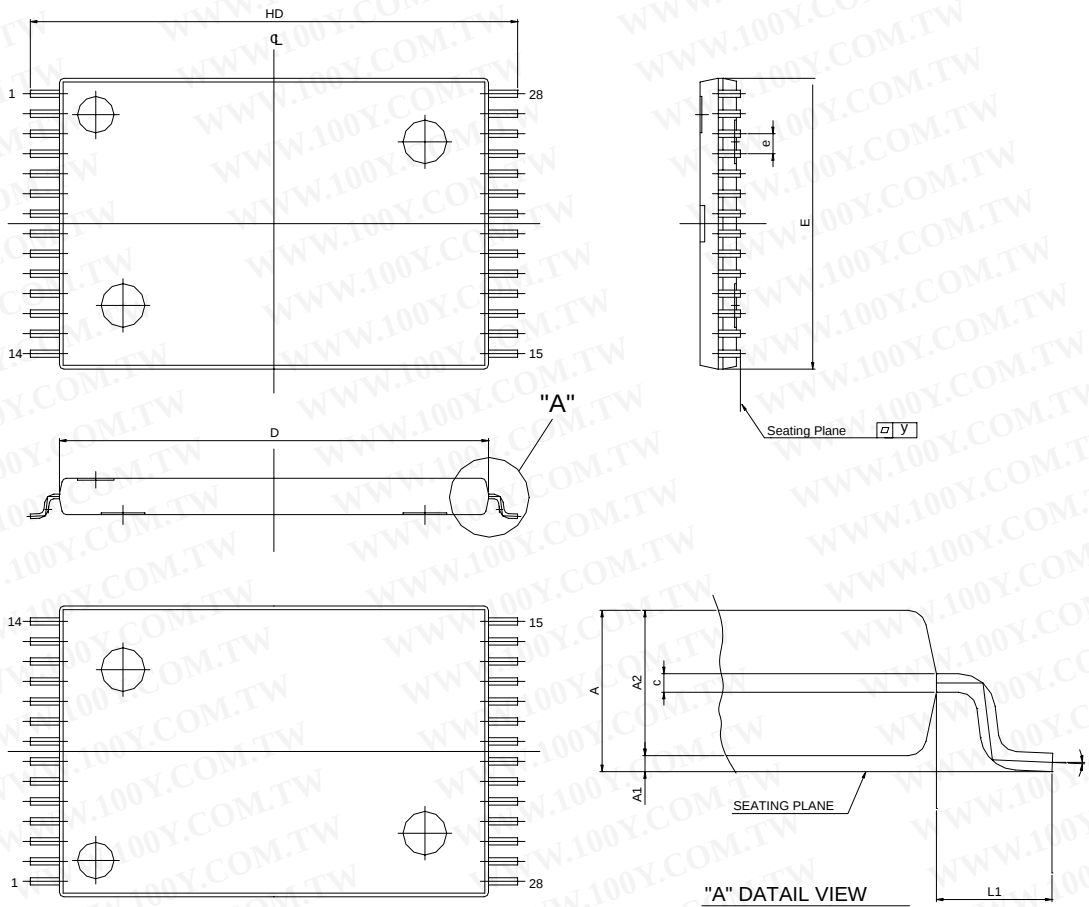


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Rev. 1.3

UT62256C 32K X 8 BIT LOW POWER CMOS SRAM

28 pin 8x13.4mm STSOP Package Outline Dimension



SYMBOL \ UNIT	INCH(BASE)	MM(REF)
A	0.047 (MAX)	1.20 (MAX)
A1	0.004 ±0.002	0.10 ±0.05
A2	0.039 ±0.002	1.00 ±0.05
D	0.465 ±0.004	11.800 ±0.100
E	0.315 ±0.004	8.000 ±0.100
e	0.022 (TYP)	0.55 (TYP)
HD	0.528 ±0.008	13.40 ±0.20
L1	0.0315 ±0.004	0.80 ±0.10
y	0.003 (MAX)	0.076 (MAX)
θ	0° 5°	0° 5°

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Rev. 1.3

UT62256C
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PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) typ.	PACKAGE
UT62256CPC-70	70	0.3mA	28PIN PDIP
UT62256CPC-70L	70	2 μ A	28PIN PDIP
UT62256CPC-70LL	70	1 μ A	28PIN PDIP
UT62256CSC-35	35	0.3mA	28PIN SOP
UT62256CSC-35L	35	2 μ A	28PIN SOP
UT62256CSC-35LL	35	1 μ A	28PIN SOP
UT62256CSC-70	70	0.3mA	28PIN SOP
UT62256CSC-70L	70	2 μ A	28PIN SOP
UT62256CSC-70LL	70	1 μ A	28PIN SOP
UT62256CLS-35	35	0.3mA	28PIN STSOP
UT62256CLS-35L	35	2 μ A	28PIN STSOP
UT62256CLS-35LL	35	1 μ A	28PIN STSOP
UT62256CLS-70	70	0.3mA	28PIN STSOP
UT62256CLS-70L	70	2 μ A	28PIN STSOP
UT62256CLS-70LL	70	1 μ A	28PIN STSOP

ORDERING INFORMATION (for lead free product)

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) typ.	PACKAGE
UT62256CPCL-70	70	0.3mA	28PIN PDIP
UT62256CPCL-70L	70	2 μ A	28PIN PDIP
UT62256CPCL-70LL	70	1 μ A	28PIN PDIP
UT62256CSCL-35	35	0.3mA	28PIN SOP
UT62256CSCL-35L	35	2 μ A	28PIN SOP
UT62256CSCL-35LL	35	1 μ A	28PIN SOP
UT62256CSCL-70	70	0.3mA	28PIN SOP
UT62256CSCL-70L	70	2 μ A	28PIN SOP
UT62256CSCL-70LL	70	1 μ A	28PIN SOP
UT62256CLSL-35	35	0.3mA	28PIN STSOP
UT62256CLSL-35L	35	2 μ A	28PIN STSOP
UT62256CLSL-35LL	35	1 μ A	28PIN STSOP
UT62256CLSL-70	70	0.3mA	28PIN STSOP
UT62256CLSL-70L	70	2 μ A	28PIN STSOP
UT62256CLSL-70LL	70	1 μ A	28PIN STSOP



Rev. 1.3

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